

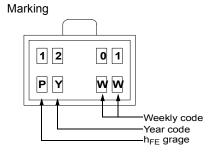
# **KSA1201 PNP Epitaxial Silicon Transistor**

## **Power Amplifier**

- Collector-Emitter Voltage: V<sub>CEO</sub>= -120V
- f<sub>T</sub>=120MHz
- Collector Power Dissipation P<sub>C</sub>=1~2W : Mounted on Ceramic Board
- · Complement to KSC2881



1. Base 2. Collector 3. Emitter



## Absolute Maximum Ratings T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>CBO</sub>	Collector Base Voltage	-120	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-120	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current	-800	mA
I <sub>B</sub>	Base Current	-160	mA
P <sub>C</sub> P <sub>C</sub> *	Collector Power Dissipation	500 1,000	mW mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

<sup>\*</sup> Mounted on Ceramic Board (250mm² x 0.8mm)

### Electrical Characteristics T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -10mA, I <sub>B</sub> = 0	-120			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = -1 \text{mA}, I_C = 0$	-5			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = -120V, I <sub>E</sub> = 0			-100	nA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{BE} = -5V, I_{C} = 0$			-100	nA
h <sub>FE</sub>	DC Current Gain	$V_{CE} = -5V, I_{C} = -100 \text{mA}$	80		240	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA			-1.0	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	$V_{CE} = -5V, I_{C} = -500 \text{mA}$			-1.0	V
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = -5V, I_{C} = -100 \text{mA}$		120		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = -10V, I <sub>E</sub> = 0, f = 1MHz			30	pF

# h<sub>FE</sub> Classification

Classification	0	Y	
h <sub>FE</sub>	80 ~ 160	120 ~ 240	

# Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
1201	1201 KSA1201		13"		4,000

## **Typical Performance Characteristics**

Figure 1. Static Characteristic

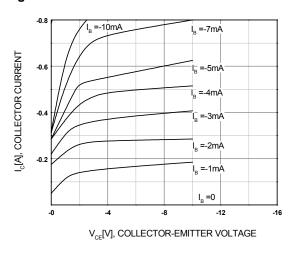
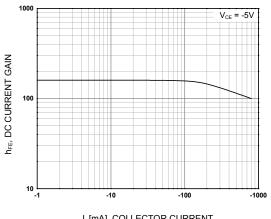


Figure 2. DC Current Gain



 $I_c[mA]$ , COLLECTOR CURRENT

Figure 3. Collector-Emitter Saturation Voltage

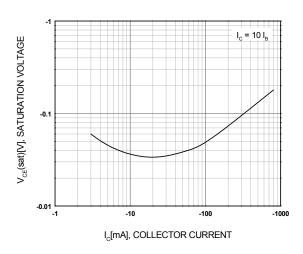


Figure 4. Base-Emitter On Voltage

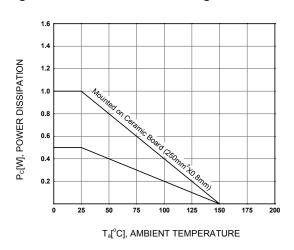


Figure 5. Safe Operating Area

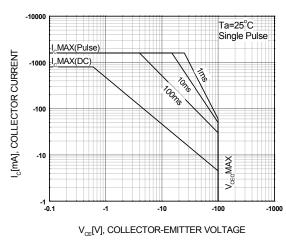
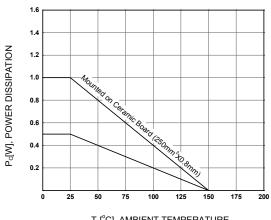


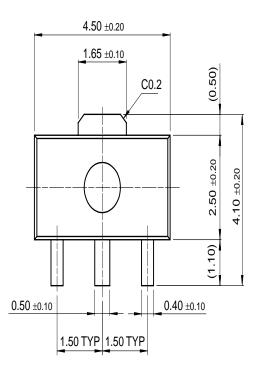
Figure 6. Power Derating

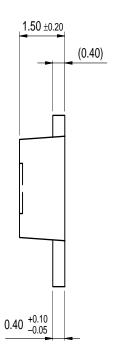


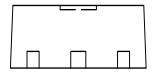
T<sub>a</sub>[°C], AMBIENT TEMPERATURE

# **Mechanical Dimensions**

# **SOT-89**







Dimensions in Millimeters

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